IN THE CLAIMS:

Please cancel claims 9, 20, 22, 23, and 31 without prejudice and amend the claims as follows:

1-7. (Canceled)

8. (Currently amended) A method for planarizing an organosilicate layer, comprising:

positioning a substrate having an organosilicate layer thereon in a polishing system;

providing a slurry including an abrasive material selected from the group consisting of silica (SiO_2), aluminum oxide (Al_2O_3), zirconium oxide (ZrO_2), titanium oxide (TiO_2), and combinations thereof dispersed in a solvent to the polishing system, wherein the slurry has a pH greater than about 9.0; and

polishing the organosilicate layer using the slurry.

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9. (Canceled)

10. (Original) The method of claim 8 wherein the abrasive material has an average particle size greater than about 35 nm (nanometers).

11. (Original) The method of claim 8 wherein the pH of the slurry is adjusted by adding a source of hydroxyl ions thereto.

12. (Currently amended) The method of claim 11 wherein the source of hydroxyl ions is selected from the group consisting of potassium hydroxide (KOH), ammonium hydroxide (NH_4OH), sodium hydroxide (NaOH), calcium hydroxide (CaOH), magnesium hydroxide (MgOH), and combinations thereof.

13. (Original) The method of claim 8 wherein the slurry further comprises one or more materials selected from the group consisting of chelating agents, buffers, oxidizers, corrosion inhibitors, and combinations thereof.

14. (Original) The method of claim 8 wherein the concentration of abrasive material in the slurry is within a range of about 10% by weight to about 60% by weight.

15. (Original) The method of claim 8 wherein the organosilicate layer is polished by placing it in contact with a polishing pad, the polishing pad having the slurry thereon, and wherein the polishing pad is disposed upon a rotatable platen.

16. (Original) The method of claim 15 wherein the polishing pad comprises polyurethane.

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17. (Original) The method of claim 15 wherein the organosilicate layer contacts the polishing pad with a pressure within range of about 1 psi (pounds/square inch) to about 14 psi.

18. (Original) The method of claim 15 wherein the platen rotates at a speed within the range of about 0.1 m/s (meters/second) to about 2 m/s.

19. (Currently amended) A method for fabricating a device, comprising:

providing a substrate having conductive features formed thereon with an organosilicate layer deposited between and on top of the conductive features;

positioning the substrate in a polishing system;

providing a slurry including an abrasive material selected from the group consisting of silica (SiO_2), aluminum oxide (Al_2O_3), zirconium oxide (ZrO_2), titanium oxide (TiO_2), and combinations thereof dispersed in a solvent and potassium hydroxide (KOH) to the polishing system, wherein the slurry has a pH greater than about 9; and

polishing the organosilicate layer using the slurry.

20. (Canceled)

21. (Original) The method of claim 19 wherein the abrasive material has an average particle size greater than about 35 nm (nanometers).

22. (Canceled)

23. (Canceled)

24. (Original) The method of claim 19 wherein the slurry further comprises one or more materials selected from the group consisting of chelating agents, buffers, oxidizers, corrosion inhibitors, and combinations thereof.

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25. (Original) The method of claim 19 wherein the concentration of abrasive material in the slurry is within a range of about 10% by weight to about 60% by weight.

26. (Original) The method of claim 19 wherein the organosilicate layer is polished by placing it in contact with a polishing pad having the slurry thereon, and wherein the polishing pad is disposed upon a rotatable platen.

27. (Original) The method of claim 26 wherein the polishing pad comprises polyurethane.

28. (Original) The method of claim 26 wherein the organosilicate layer contacts the polishing pad with a pressure within a range of about 1 psi (pounds/square inch) to about 4 psi.

29. (Original) The method of claim 26 wherein the platen rotates at a speed within a range of about 0.1 m/s (meters/second) to about 2.0 m/s.

30. (Currently amended) A method for planarizing an organosilicate layer, comprising:

positioning a substrate having an organosilicate layer thereon in a polishing system;

providing a slurry including an abrasive material selected from the group consisting of silica (SiO_2), aluminum oxide (Al_2O_3), zirconium oxide (ZrO_2), titanium oxide (TiO_2), and combinations thereof having an average particle size greater than about 35 nm and dispersed in a solvent to the polishing system, wherein the slurry has a pH greater than about 9.0 and the concentration of the abrasive material in the slurry is within a range of about 10% by weight to about 60% by weight; and polishing the organosilicate layer using the slurry.

31. (Canceled) The method of claim 30 wherein the abrasive material is selected from the group consisting of silica (SiO_2), aluminum oxide (Al_2O_3), zirconium oxide (ZrO_2), titanium oxide (TiO_2), and combinations thereof.

32. (Previously Presented) The method of claim 30, wherein the pH of the slurry is adjusted by adding a source of hydroxyl ions thereto.

33. (Currently amended) The method of claim 32, wherein the source of hydroxyl ions is selected from the group consisting of potassium hydroxide (KOH), ammonium hydroxide (NH_4OH), sodium hydroxide (NaOH), calcium hydroxide (CaOH), magnesium hydroxide (MgOH), and combinations thereof.

34. (Previously Presented) The method of claim 30, wherein the slurry further comprises one or more materials selected from the group consisting of chelating agents, buffers, oxidizers, corrosion inhibitors, and combinations thereof.

35. (Previously Presented) The method of claim 30, wherein the organosilicate layer is polished by placing it in contact with a polishing pad, the polishing pad having the slurry thereon, and wherein the polishing pad is disposed upon a rotatable platen.

36. (Previously Presented) The method of claim 35, wherein the organosilicate layer contacts the polishing pad with a pressure within range of about 1 psi (pounds/square inch) to about 14 psi.